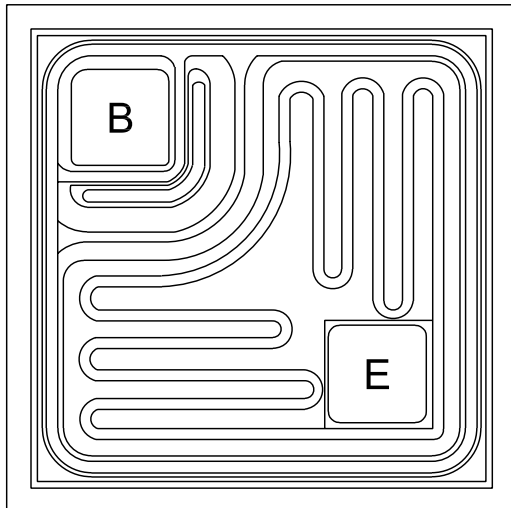


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	23 x 23 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.7 x 4.7 MILS
Emitter Bonding Pad Area	4.7 x 4.7 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE: COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

33,085

PRINCIPAL DEVICE TYPES

2N6426
2N6427
CMPT6427
CMPTA13
CMPTA14
CXTA14
CZTA14
MPSA13
MPSA14

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R0 (24 -August 2005)